1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-1060

2. Structure :

2-1. Planar type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy.

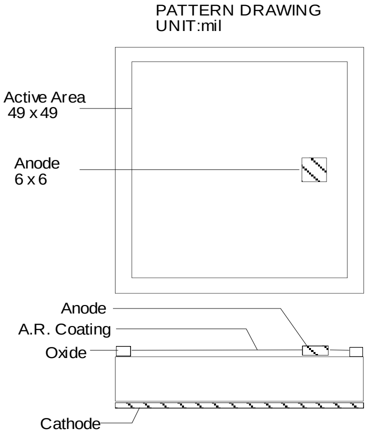
3. Size :

3-1. Chip size : 60 mils × 60 mils (1.524 mm × 1.524 mm).
3-2. Chip thickness : 12 ± 1.5mils (0.305 ± 0.038 mm).
3-3. Active area : 49 mils × 49 mils (1.245 mm × 1.245 mm).
3-4. Bonding pad (Anode) :. 6 mils × 6 mils (0.15 mm × 0.15 mm).
3-5. Pattern drawing : refer to the attached drawing.

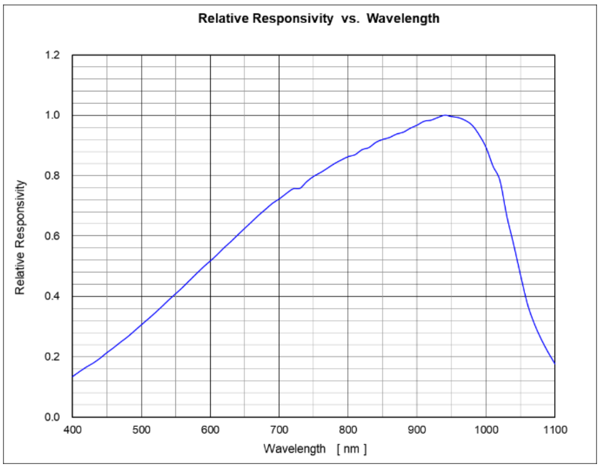
4. Electro-optical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark Current	I_D	V_R=10V Ee=0mW/cm^2			10	nA
※Reverse breakdown Voltage	$V_{(BR)R}$	I_R=100uA Ee=0mW/cm^2	33			V
Open circuit Voltage	Voc	T=2856K Ee=5mW/cm^2		410		mV
Short circuit Current	Isc	T=2856K Ee=5mW/cm^2		16		µA
Reverse light Current	IL	V_R =5V T=2856K Ee=5mW/cm^2		16		µA
Total Capacitance	Ct	V_R =5V Ee=0mW/cm^2 f=1MHz		6		pF

※Based on 100% probing



5. Relative spectral responsivity



※Bare chip measured with integrating sphere, for reference only.